

## Exhibition

A technical exhibition will be held during the conference. Companies that provide materials, devices, equipment and services for testing, characterization, production and development of SiC and wide-bandgap materials are encouraged to exhibit at the conference.

Further information can be found on our website. For further details regarding the exhibition, please contact :

[sponsor@icscrm2015.org](mailto:sponsor@icscrm2015.org)

## Further information

A final circular will be distributed in February 2015. For the latest information, please visit our website or contact:

[info@icscrm2015.org](mailto:info@icscrm2015.org)



## International steering committee

### Members

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## Local organizing committee

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*Francesco La Via* (CNR-IMM), Co-Chair, Program Chair  
*Roberta Nipoti* (CNR-IMM), Proceeding Chair  
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*Filippo Giannazzo* (CNR-IMM), Sponsor/Exhibitors Co-chair  
*Mario Saggio* (STMicroelectronics), Industrial Session Chair  
*Aldo Spada* (CNR-IMM), Webmaster

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## First announcement and call for papers

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## International Conference on Silicon Carbide and Related Materials 2015



**Giardini Naxos (Italy)**  
**4 – 9 October 2015**



**Consiglio Nazionale delle Ricerche**

**[www.icscrm2015.org](http://www.icscrm2015.org)**

## Scope

The aim of the conference is to discuss recent advances in theoretical and experimental investigations of crystal growth, characterization and control of material properties, as well as other basic research issues concerning wide bandgap semiconductors such as silicon carbide (SiC), III-nitrides, diamond and their related materials such as graphene.

New research results relevant to wafer production processes, device fabrication technologies and device applications will also be presented and discussed. The objective is to promote the production and commercialization of advanced devices and systems used for low on-resistance - high voltage switching, high frequency - high power amplification and high temperature operation.

The conference also serves as an international forum for the exchange of ideas on recent scientific and technical issues among researchers and engineers in industrial, academic and public sectors.



## Topics

- Fundamentals (Theoretical and Experimental)
- Bulk and Epitaxial Growth
- New Materials Grown on SiC (Such as Graphene)
- III-nitrides and Diamond
- Material Characterization
- Surfaces and Interfaces
- Device Fabrication Processes
- Devices (Power switching, RF power, High temperature, Radiation-Resistant Devices, optical devices, photovoltaic devices, MEMS, ..etc.)
- Device Physics (Measurement, Modeling, Simulation, and Reliability)
- Packaging, Modular, and Circuit Technology
- System Applications

## Important dates

- May 9<sup>th</sup>, 2015: Deadline for abstract submission
- July 1<sup>st</sup>, 2015: Notification of acceptance of regular papers
- July 31<sup>th</sup>, 2015: Early Registration deadline
- August 14<sup>th</sup>, 2015: Deadline for late news submission
- August 31<sup>st</sup>, 2015: Notification of acceptance of late news

## Note to authors

The official language of the conference is English, which will be used for all presentations and printed materials. Authors are expected to present their papers in person at the conference. If authors cannot attend or wish to withdraw their paper, the technical program chair must be notified well in advance.

## Publication of papers

The proceedings will be published in Materials Science Forum. The authors of accepted papers will be asked to submit manuscripts before the conference to facilitate refereeing. The manuscript format and detailed instructions will be forwarded to the authors at the time of notification of acceptance.



## Location

ICSCRM 2015 will be held in the Congress Center of the Atahotel Naxos Beach, in Giardini Naxos, Italy. Giardini Naxos is a small city situated on the East Coast of Sicily. Its historical origins date back to 735 b.C. when a group of settlers founded what is indicated as the first Greek colony in Sicily. The Atahotel Naxos Beach is built over an area dominated by the Etna Volcano and shading off to the sea. The whole complex is surrounded by a huge park of citrus fruits, olive groves and many kinds of flowers. The Hotel is located in a strategic position, starting point to discover Sicily and its wonderful attractions, such as Taormina (6km), the mount Etna (the highest active volcano in Europe), Catania and Syracuse.

## Official website

For further details on Giardini Naxos and ICSCRM 2015, you are kindly encouraged to visit the conference website at :

[www.icscrm2015.org](http://www.icscrm2015.org)